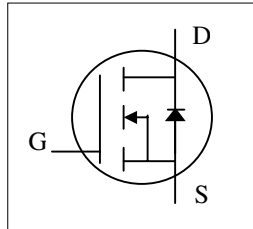




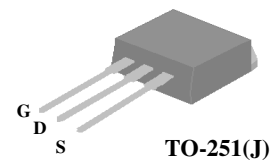
- ▼ Lower Gate Charge
- ▼ 100% Avalanche Rated
- ▼ Fast Switching Performance
- ▼ Simple Drive Requirement



| | |
|--------------|-------------|
| BV_{DSS} | 400V |
| $R_{DS(ON)}$ | 16 Ω |
| I_D | 0.5A |

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.



The TO-251 package is widely preferred for commercial-industrial through-hole applications.

Absolute Maximum Ratings

| Symbol | Parameter | Rating | Units |
|-----------------------|--|------------|---------------|
| V_{DS} | Drain-Source Voltage | 400 | V |
| V_{GS} | Gate-Source Voltage | ± 20 | V |
| $I_D@T_C=25^\circ C$ | Continuous Drain Current, V_{GS} @ 10V | 0.5 | A |
| $I_D@T_C=100^\circ C$ | Continuous Drain Current, V_{GS} @ 10V | 0.4 | A |
| I_{DM} | Pulsed Drain Current ¹ | 2 | A |
| $P_D@T_C=25^\circ C$ | Total Power Dissipation | 17.4 | W |
| | Linear Derating Factor | 0.14 | W/ $^\circ C$ |
| E_{AS} | Single Pulse Avalanche Energy ² | 0.5 | mJ |
| T_{STG} | Storage Temperature Range | -55 to 150 | $^\circ C$ |
| T_J | Operating Junction Temperature Range | -55 to 150 | $^\circ C$ |

Thermal Data

| Symbol | Parameter | Value | Units |
|--------|--|-------|--------------|
| Rthj-c | Maximum Thermal Resistance, Junction-case | 7.2 | $^\circ C/W$ |
| Rthj-a | Maximum Thermal Resistance, Junction-ambient | 110 | $^\circ C/W$ |



Electrical Characteristics@T_j=25°C(unless otherwise specified)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|---------------------|--|--|------|------|------|-------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =1mA | 400 | - | - | V |
| R _{DS(ON)} | Static Drain-Source On-Resistance ³ | V _{GS} =10V, I _D =0.5A | - | - | 16 | Ω |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} , I _D =250uA | 1 | - | 3 | V |
| g _{fs} | Forward Transconductance | V _{DS} =10V, I _D =0.5A | - | 0.5 | - | S |
| I _{DSS} | Drain-Source Leakage Current (T _j =25°C) | V _{DS} =400V, V _{GS} =0V | - | - | 10 | uA |
| | Drain-Source Leakage Current (T _j =150°C) | V _{DS} =320V, V _{GS} =0V | - | - | 100 | uA |
| I _{GSS} | Gate-Source Leakage | V _{GS} =±20V | - | - | ±100 | nA |
| Q _g | Total Gate Charge ³ | I _D =1A | - | 2.9 | 4.6 | nC |
| Q _{gs} | Gate-Source Charge | V _{DS} =320V | - | 0.6 | - | nC |
| Q _{gd} | Gate-Drain ("Miller") Charge | V _{GS} =10V | - | 0.6 | - | nC |
| t _{d(on)} | Turn-on Delay Time ³ | V _{DD} =200V | - | 7.7 | - | ns |
| t _r | Rise Time | I _D =1A | - | 12 | - | ns |
| t _{d(off)} | Turn-off Delay Time | R _G =3.3Ω, V _{GS} =10V | - | 23 | - | ns |
| t _f | Fall Time | R _D =200Ω | - | 73 | - | ns |
| C _{iss} | Input Capacitance | V _{GS} =0V | - | 76 | 125 | pF |
| C _{oss} | Output Capacitance | V _{DS} =25V | - | 11 | - | pF |
| C _{rss} | Reverse Transfer Capacitance | f=1.0MHz | - | 4 | - | pF |

Source-Drain Diode

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|-----------------|---------------------------------|---|------|------|------|-------|
| V _{SD} | Forward On Voltage ³ | I _S =2A, V _{GS} =0V | - | - | 1.5 | V |
| t _{rr} | Reverse Recovery Time | I _S =1A, V _{GS} =0V | - | 260 | - | ns |
| Q _{rr} | Reverse Recovery Charge | dI/dt=100A/μs | - | 460 | - | nC |

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Starting T_j=25°C , V_{DD}=50V , L=1mH , R_G=25Ω
- 3.Pulse test

THIS PRODUCT IS AN ELECTROSTATIC SENSITIVE, PLEASE HANDLE WITH CAUTION.

THIS PRODUCT HAS BEEN QUALIFIED FOR CONSUMER MARKET. APPLICATIONS OR USES AS CRITERIAL COMPONENT IN LIFE SUPPORT DEVICE OR SYSTEM ARE NOT AUTHORIZED.

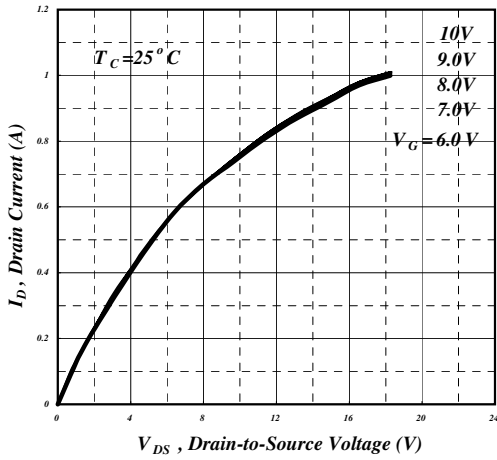


Fig 1. Typical Output Characteristics

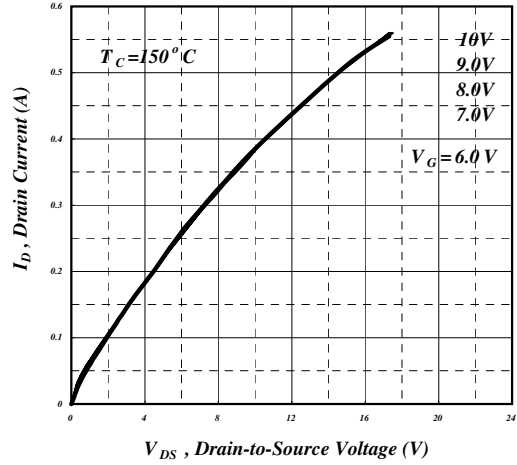


Fig 2. Typical Output Characteristics

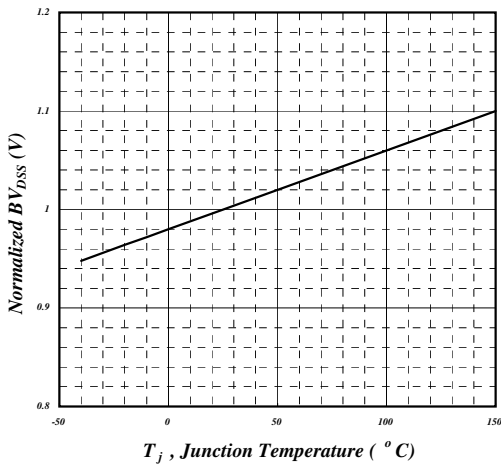


Fig 3. Normalized BV_{DSS} v.s. Junction Temperature

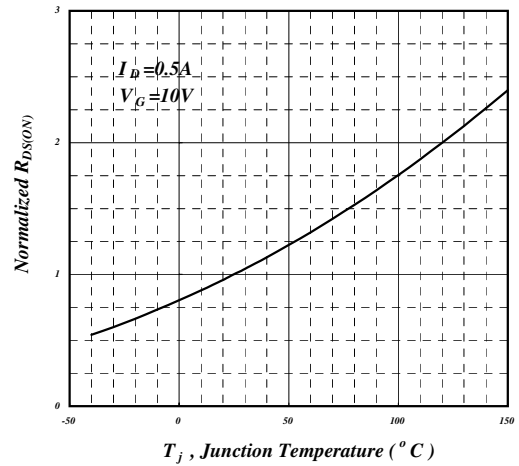


Fig 4. Normalized On-Resistance v.s. Junction Temperature

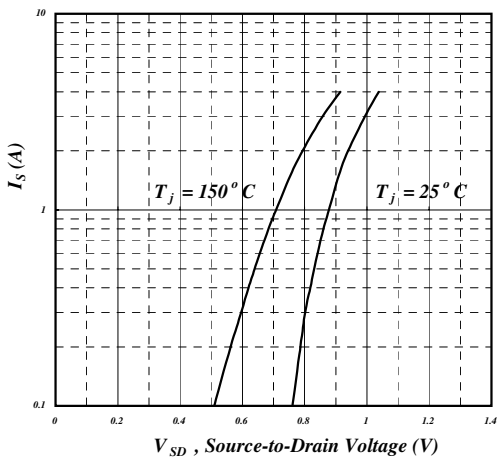


Fig 5. Forward Characteristic of Reverse Diode

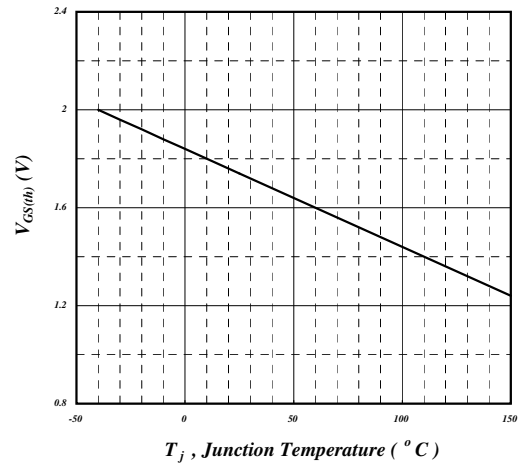


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

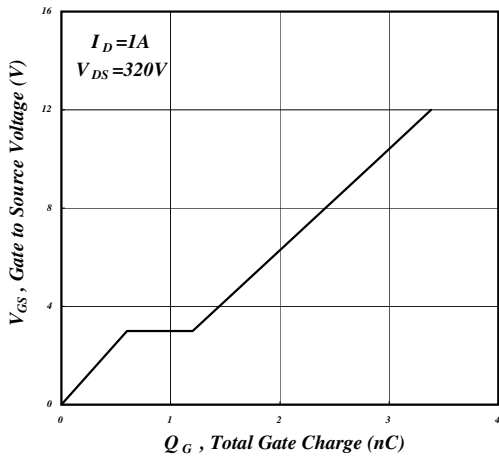


Fig 7. Gate Charge Characteristics

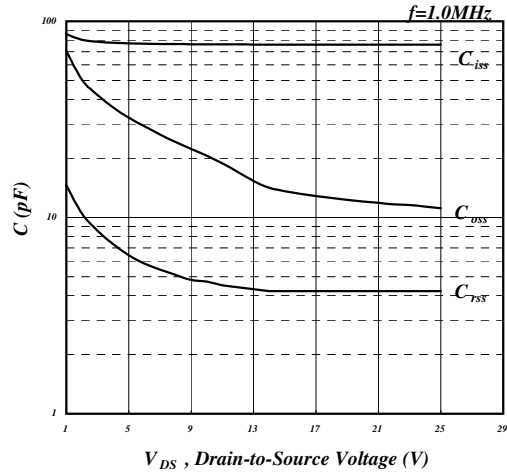


Fig 8. Typical Capacitance Characteristics

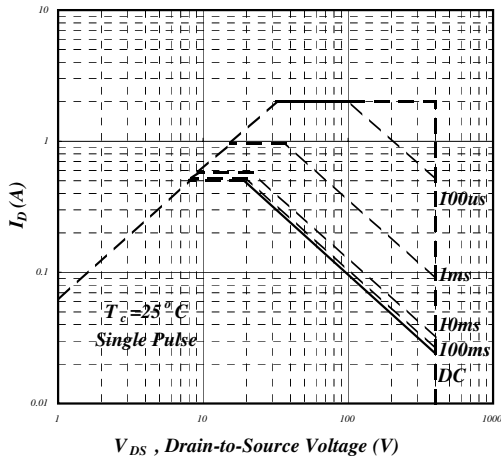


Fig 9. Maximum Safe Operating Area

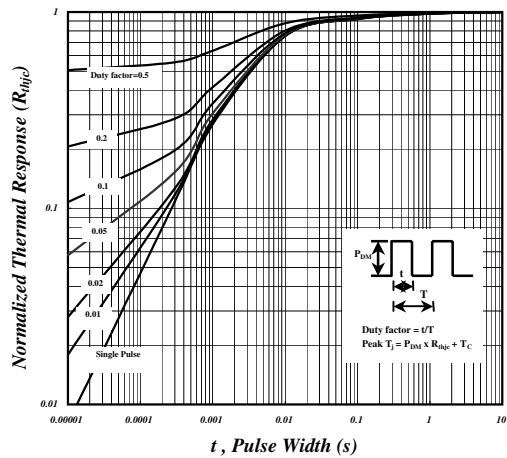


Fig 10. Effective Transient Thermal Impedance

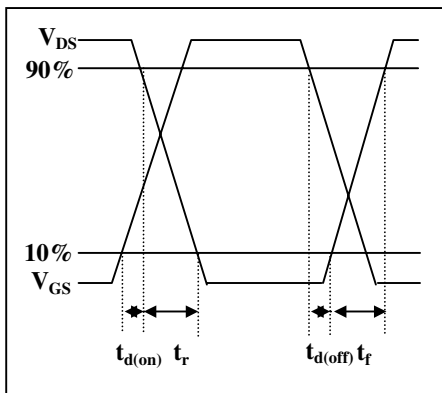


Fig 11. Switching Time Waveform

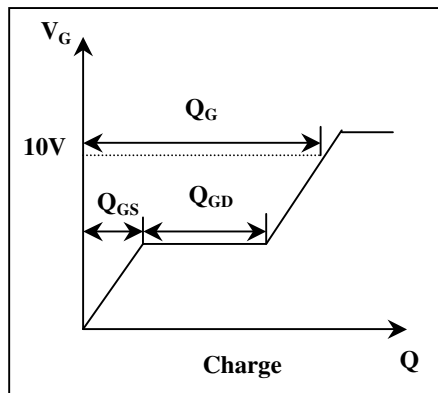


Fig 12. Gate Charge Waveform